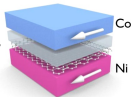


# Atomic Layer Deposition (ALD) in Magnetism and Spintronics

**Michal Staňo**

[michal.stano@ceitec.vutbr.cz](mailto:michal.stano@ceitec.vutbr.cz)



**Magnetism group winter retreat**  
Vlachovice



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EUROPEAN UNION  
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Operational Programme Research,  
Development and Education

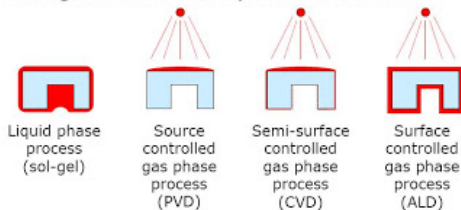


# Outline of the presentation

- 1 Atomic Layer Deposition
- 2 Use of Atomic layer deposition in spintronics
- 3 STAFF3d-spin project
- 4 Summary

# Atomic Layer Deposition

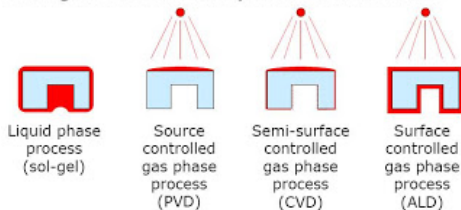
## Coating thickness uniformity with different methods



[beneq.com](http://beneq.com)

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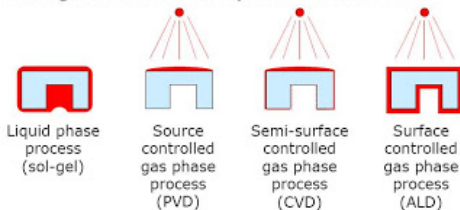


[beneq.com](http://beneq.com)

- Special mode of Chemical Vapor Deposition (CVD)
- Sequential self-limiting surface chemical reactions
- **Conformal coating** of rough surfaces, holes, pillars, . . .
- **Precise control over film thickness** ( $\approx 0.1$  nm per cycle)

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ALD Review: [George, Chem. Rev. 110, 111-131 \(2010\)](#)

Various info: [www.plasma-ald.com](http://www.plasma-ald.com)

Conformal coating possible also in a solution – electroless plating

# What materials can be deposited by ALD?

Close to everything:

- nitrides, oxides [ $\text{AlO}_x$ ]
- metals, including Fe, Co, Ni, Pt, W, Ta, Ru, Rh, . . .
- alloys, ternary and more complex compounds

List of materials: [Miikkulainen et al., JAP 113, 021301 \(2013\)](#)

# ALD cooking: Recipe and ingredients

ALD deposition – what is needed

- **vessel:** reactor (rough vacuum, temperature control, gas inlets)
- **ingredients:** precursors and reactants
- **energy:** temperature and/or plasma
- **recipe** (process parameters: how much, how long, ...)



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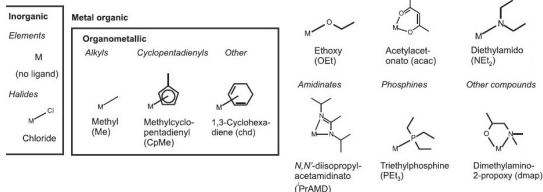
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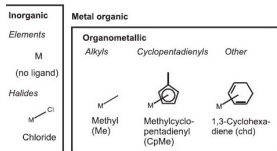
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Alkoxides



Ethoxy (OEt)

$\beta$ -Diketones



Acetylacetonato (acac)

Amides and imides



Diethylamido (NEt<sub>2</sub>)

Amidates



*N,N'*-diisopropylacetamidinato (PrAMD)

Phosphines



Triethylphosphine (PEt<sub>3</sub>)

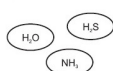
Other compounds



Dimethylamino-2-propoxy (dmap)

(a) precursors – mostly metallo-organics

Hydrides



Molecular elements



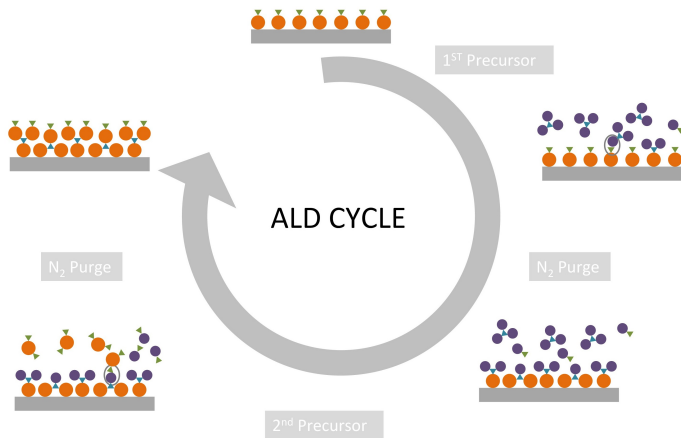
Other



Miikkulainen et al., *JAP* 113, 021301 (2013)

(b) reactants

# ALD cycle – How it works



ctechnano.com

See also <https://www.plasma-ald.com/>

# ALD in spintronics / magnetism

- [microelectronics]: insulating, protective layers ( $\text{AlO}_x$ ),  
conductive seed layers (Cu, Co, Ru)
- spin-Hall-active Pt thin films (order of magnitude worse  
than sputtered Pt, but detectable & room for improvement)  
[APL 112, 242403 \(2018\)](#)
- **oxide barrier in magnetic tunnel junctions**
- **magnetic nanotubes**

## Oxide barrier in magnetic tunnel junctions

Magnetic Tunnel Junction (MTJ): magnet/insulator/magnet

Tunneling MagnetoResistance (TMR =  $\frac{R_{\uparrow\downarrow}(H) - R_{\uparrow\uparrow}}{R_{\uparrow\uparrow}}$ ) 100s % @ RT

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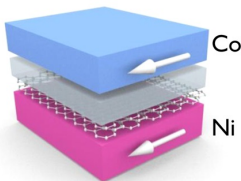
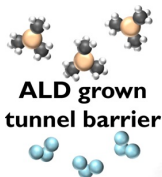
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2D materials (graphene, black P)  
+  $\leq 1 \text{ nm}$  ALD barrier in MTJs  
*ACS Nano* **8**(8), 7890-7895 (2014)

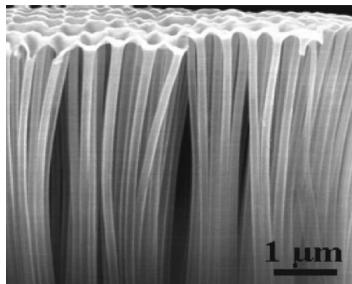
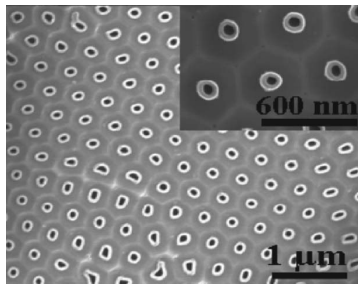
# Magnetic nanotubes deposited using ALD

Ni, Co Nanotubes: *JAP* **111**, 09J111 (2007)

Template: pore diameter 35 nm and 160 nm, length 2-50  $\mu\text{m}$

Precursor: nickelocene ( $\text{NiCp}_2$ )+ $\text{H}_2\text{O}$  vapour – gives oxide

Reduction better after ALD –  $\text{Ar}+5\% \text{H}_2$  (lower grain size)



SEM images:  $\text{TiO}_2/\text{Ni}/\text{TiO}_2$  tubes. Left: in template (top-view), Right: liberated.

# STAFF3d-spin project

Synthesis and investigation of  
**Synthetic Tubular AntiFerromagnets For 3D Spintronics**

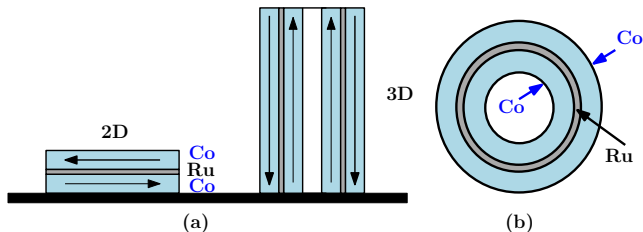


# STAFF3d-spin project

## Synthesis and investigation of Synthetic Tubular AntiFerromagnets For 3D Spintronics

### Goals:

- preparation 3D vertical arrays of tubular SAF (ALD, electroless dep.)
- test of interfaces suitability for spintronics (giant magnetoresistance)
- investigation of individual magnetic nanotubes, tubular SAFs



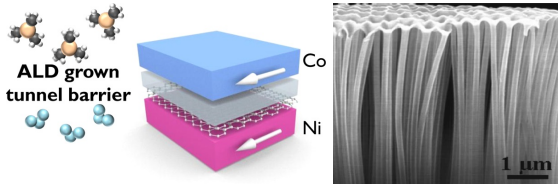
Synthetic anti-ferromagnets. (a) current planar structure (Ru  $t \approx 1$  nm) versus proposed 3D vertical structure. (b) Cross-section view on the 3D tubular structure.

## Summary: ALD in spintronics/magnetism

- + conformal coating, high-aspect ratio structures (even 1000:1)
- + precise control over thickness, easy for core-shell
  - slow, not suitable for thicker coatings ( $\geq 100$  nm)
  - typically highly granular
  - challenge: high purity, good magnetic properties

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- **slow**, not suitable for thicker coatings ( $\geq 100$  nm)
- **typically highly granular**
- **challenge: high purity**, good magnetic properties



- still **mostly oxides** (cover layers, barriers in MTJs)
- first tests with **Pt for spintronics** (spin Hall effect)
- deposition of **magnetic nanotubes**, but mostly oxides or reduces from oxides (lower quality)
- only few magnetic measurements on ALD magnets (VSM)

# Acknowledgements

**Thank you for your attention!**

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